FHD010

NPN Silicon Darlington High Power Transistor

Features:

1. Using triple-diffusion process.High output current. Small driving power.
2. Highest amplification factor. High inverse voltage.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for current output,voltage adjustment and servo circuit of numerical control machine.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications										Test Condition
			A	B	C	D	E	F	G	H	I	J	
Collector-Emitter Voltage	V_{CEO}	V	100	200	300	400	500	600	700	800	900	1000	
Emitter-Base Voltage	V_{EBO}	V	5										
Max. Collector Current	I_{CM}	A	1.0										
Max. Collector Dissipation	P_{CM}	W	10										Tc:75°C
Junction Temperature	T_{jm}	°C	175										
Storage Temperature	T_{stg}	°C	-55~+175										
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.0										V_{CE}=100V
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2.0										I_C=0.5A,I_B=0.01A
DC Current Gain	h_{FE}		Min.:500										V_{CE}=10V,I_C=0.5A
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	100	200	300	400	500	600	700	800	900	1000	I_C=5mA
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5										I_E=5mA

Outline and Dimensions: